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- Three inbound windows plus a configuration window on PCI Express
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- Two 64-bit DDR2/DDR3 memory controllers
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 - Four banks of memory supported, each up to 4 Gbytes, for a maximum of 16 Gbytes per controller
 - DRAM chip configurations from 64 Mbits to 4 Gbits with x8/x16 data ports
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 - Page mode support
 - Up to 32 simultaneous open pages for DDR2 or DDR3
 - Contiguous or discontiguous memory mapping
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 - Sleep mode support for self-refresh SDRAM
 - On-die termination support when using DDR2 or DDR3
 - Supports auto refreshing
 - On-the-fly power management using CKE signal
 - Registered DIMM support
 - Fast memory access through JTAG port
 - 1.8-V SSTL_1.8 compatible I/O
 - Support 1.5-V operation for DDR3. The detail is TBD pending on official release of appropriate industry specifications.
 - Support for battery-backed main memory
- Programmable interrupt controller (PIC)
 - Programming model is compliant with the OpenPIC architecture.
 - Supports 16 programmable interrupt and processor task priority levels
 - Supports 12 discrete external interrupts
 - Supports 4 message interrupts per processor with 32-bit messages
 - Supports connection of an external interrupt controller such as the 8259 programmable interrupt controller
 - Four global high resolution timers/counters per processor that can generate interrupts
 - Supports a variety of other internal interrupt sources



Overview

- Ability to launch DMA from single write transaction
- Serial RapidIO interface unit
 - Supports RapidIO Interconnect Specification, Revision 1.2
 - Both 1x and 4x LP-serial link interfaces
 - Long- and short-haul electricals with selectable pre-compensation
 - Transmission rates of 1.25, 2.5, and 3.125 Gbaud (data rates of 1.0, 2.0, and 2.5 Gbps) per lane
 - Auto-detection of 1x- and 4x-mode operation during port initialization
 - Link initialization and synchronization
 - Large and small size transport information field support selectable at initialization time
 - 34-bit addressing
 - Up to 256 bytes data payload
 - All transaction flows and priorities
 - Atomic set/clr/inc/dec for read-modify-write operations
 - Generation of IO_READ_HOME and FLUSH with data for accessing cache-coherent data at a remote memory system
 - Receiver-controlled flow control
 - Error detection, recovery, and time-out for packets and control symbols as required by the RapidIO specification
 - Register and register bit extensions as described in part VIII (Error Management) of the RapidIO specification
 - Hardware recovery only
 - Register support is not required for software-mediated error recovery.
 - Accept-all mode of operation for fail-over support
 - Support for RapidIO error injection
 - Internal LP-serial and application interface-level loopback modes
 - Memory and PHY BIST for at-speed production test
- RapidIO–compliant message unit
 - 4 Kbytes of payload per message
 - Up to sixteen 256-byte segments per message
 - Two inbound data message structures within the inbox
 - Capable of receiving three letters at any mailbox
 - Two outbound data message structures within the outbox
 - Capable of sending three letters simultaneously
 - Single segment multicast to up to 32 devIDs
 - Chaining and direct modes in the outbox
 - Single inbound doorbell message structure
 - Facility to accept port-write messages



RESET Initialization

Table 8. DDRCLK AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} of 3.3V ± 5%.

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
DDRCLK jitter	_			+/- 150	ps	4, 5, 6

Notes:

- 1. **Caution:** The DDR complex clock to DDRCLK ratio settings must be chosen such that the resulting DDR complex clock frequency does not exceed the maximum or minimum operating frequencies. Refer to Section 19.4, "DDR/DDRCLK PLL Ratio," for ratio settings.
- 2. Rise and fall times for DDRCLK are measured at 0.6 V and 2.7 V.
- 3. Timing is guaranteed by design and characterization.
- 4. This represents the total input jitter—short term and long term—and is guaranteed by design.
- 5. The DDRCLK driver's closed loop jitter bandwidth should be <500 kHz at -20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track DDRCLK drivers with the specified jitter.
- 6. For spread spectrum clocking, guidelines are +0% to -1% down spread at a modulation rate between 20 kHz and 60 kHz on DDRCLK.

4.5 Platform to eTSEC FIFO Restrictions

Note the following eTSEC FIFO mode maximum speed restrictions based on platform (CCB) frequency.

For FIFO GMII modes (both 8 and 16 bit) and 16-bit encoded FIFO mode:

FIFO TX/RX clock frequency <= platform clock (CCB) frequency/4.2

For example, if the platform (CCB) frequency is 533 MHz, the FIFO TX/RX clock frequency should be no more than 127 MHz.

For 8-bit encoded FIFO mode:

FIFO TX/RX clock frequency <= platform clock (CCB) frequency/3.2

For example, if the platform (CCB) frequency is 533 MHz, the FIFO TX/RX clock frequency should be no more than 167 MHz.

4.6 Other Input Clocks

For information on the input clocks of other functional blocks of the platform, such as SerDes and eTSEC, see the respective sections of this document.

5 **RESET** Initialization

Table 9 describes the AC electrical specifications for the RESET initialization timing.

Table 9. RESET Initialization Timing Specifications

Parameter/Condition		Мах	Unit	Notes
Required assertion time of HRESET	100	—	μs	2
Minimum assertion time for SRESET	3	—	SYSCLKs	1



PLL config input setup time with stable SYSCLK before HRESET negation	100	_	μs	
Input setup time for POR configs (other than PLL config) with respect to negation of HRESET	4		SYSCLKs	1
Input hold time for all POR configs (including PLL config) with respect to negation of HRESET	2	_	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of HRESET	—	5	SYSCLKs	1

Table 9. RESET Initialization Timing Specifications (continued)

Notes:

2. Reset assertion timing requirements for DDR3 DRAMs may differ.

Table 10 provides the PLL lock times.

Table	10.	PLL	Lock	Times
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Parameter/Condition	Symbol	Min	Typical	Max
PLL lock times	_	100	μs	—
Local bus PLL	_	50	μs	_

6 DDR2 and DDR3 SDRAM Controller

This section describes the DC and AC electrical specifications for the DDR2 and DDR3 SDRAM controller interface of the MPC8572E. Note that the required $GV_{DD}(typ)$ voltage is 1.8Vor 1.5 V when interfacing to DDR2 or DDR3 SDRAM, respectively.

6.1 DDR2 and DDR3 SDRAM Interface DC Electrical Characteristics

Table 11 provides the recommended operating conditions for the DDR SDRAM controller of the MPC8572E when interfacing to DDR2 SDRAM.

Parameter/Condition	Symbol	Min	Мах	Unit	Notes
I/O supply voltage	GV _{DD}	1.71	1.89	V	1
I/O reference voltage	MV _{REF} n	$0.49 imes GV_{DD}$	$0.51 imes GV_{DD}$	V	2
I/O termination voltage	V _{TT}	MV _{REF} <i>n</i> – 0.04	$MV_{REF}n + 0.04$	V	3
Input high voltage	V _{IH}	$MV_{REF}n + 0.125$	GV _{DD} + 0.3	V	_
Input low voltage	V _{IL}	-0.3	MV _{REF} n – 0.125	V	_
Output leakage current	I _{OZ}	-50	50	μA	4
Output high current (V _{OUT} = 1.420 V)	I _{OH}	-13.4	_	mA	—

DDDO ODDAM Late	uface DO Electula	- I O le ave et eviletie e	$f_{a,m} = O(1 - (f_{a,m})) = A = O(1)$,
DURZ SURAW INTE	rtace DU Electric	al Unaracteristics	TOT (= V = (TVD) = T A V	

^{1.} SYSCLK is the primary clock input for the MPC8572E.



Table 18. DDR2 and DDR3 SDRAM Interface Output AC Timing Specifications (continued)At recommended operating conditions with GV_{DD} of 1.8 V ± 5% for DDR2 or 1.5 V ± 5% for DDR3.

Parameter	Symbol ¹	Min	Мах	Unit	Notes
800 MHz		0.917	—		
667 MHz		1.10	—		
533 MHz		1.48	—		
400 MHz		1.95	—		
ADDR/CMD output hold with respect to MCK	t _{DDKHAX}			ns	3
800 MHz		0.917	—		
667 MHz		1.10	—		
533 MHz		1.48	—		
400 MHz		1.95	—		
MCS[n] output setup with respect to MCK	t _{DDKHCS}			ns	3
800 MHz		0.917	—		
667 MHz		1.10	—		
533 MHz		1.48	—		
400 MHz	t _{DDKHCS}	1.95	_	ns	3
MCS[n] output hold with respect to MCK	t _{DDKHCX}			ns	3
800 MHz		0.917	—		
667 MHz		1.10	—		
533 MHz		1.48	—		
400 MHz		1.95	—		
MCK to MDQS Skew	t _{DDKHMH}			ns	4
800 MHz		-0.375	0.375		
<= 667 MHz		-0.6	0.6		
MDQ/MECC/MDM output setup with respect to MDQS	t _{DDKHDS,} t _{DDKLDS}			ps	5
800 MHz		375	_		
667 MHz		450	_		
533 MHz		538	_		
400 MHz		700	_		
MDQ/MECC/MDM output hold with respect to MDQS	t _{DDKHDX,} t _{DDKLDX}			ps	5
800 MHz		375	—		
667 MHz		450	_		



Figure 4 shows the DDR2 and DDR3 SDRAM Interface output timing for the MCK to MDQS skew measurement (tDDKHMH).



Figure 4. Timing Diagram for tDDKHMH

Figure 5 shows the DDR2 and DDR3 SDRAM Interface output timing diagram.



Figure 5. DDR2 and DDR3 SDRAM Interface Output Timing Diagram



Ethernet: Enhanced Three-Speed Ethernet (eTSEC)

The Fast Ethernet Controller (FEC) operates in MII mode only, and complies with the AC and DC electrical characteristics specified in this chapter for MII. Note that if FEC is used, eTSEC 3 and 4 are only available in SGMII mode.

8.1.1 eTSEC DC Electrical Characteristics

All MII, GMII, RMII, and TBI drivers and receivers comply with the DC parametric attributes specified in Table 23 and Table 24. All RGMII, RTBI and FIFO drivers and receivers comply with the DC parametric attributes specified in Table 24. The RGMII and RTBI signals are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Parameter	Symbol	Min	Max	Unit	Notes
Supply voltage 3.3 V	LV _{DD} TV _{DD}	3.13	3.47	V	1, 2
Output high voltage $(LV_{DD}/TV_{DD} = Min, IOH = -4.0 mA)$	VOH	2.40	LV _{DD} /TV _{DD} + 0.3	V	—
Output low voltage $(LV_{DD}/TV_{DD} = Min, IOL = 4.0 mA)$	VOL	GND	0.50	V	—
Input high voltage	V _{IH}	2.0	$LV_{DD}/TV_{DD} + 0.3$	V	—
Input low voltage	V _{IL}	-0.3	0.90	V	—
Input high current $(V_{IN} = LV_{DD}, V_{IN} = TV_{DD})$	IIH	_	40	μΑ	1, 2,3
Input low current (V _{IN} = GND)	Ι _{ΙL}	-600	_	μA	3

Table 23.	GMII.	MII. RMII.	and TBI DC	Electrical	Characteristics
	. ,	,		Liootiioui	0114140101101100

Notes:

¹ LV_{DD} supports eTSECs 1 and 2.

 2 TV_{DD} supports eTSECs 3 and 4 or FEC.

 3 The symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1.

Table 24. MII, GMII, RMII, RGMII, TBI, RTBI, and FIFO DC Electrical Characteristics

Parameters	Symbol	Min	Мах	Unit	Notes
Supply voltage 2.5 V	LV _{DD/} TV _{DD}	2.37	2.63	V	1,2
Output high voltage ($LV_{DD}/TV_{DD} = Min, IOH = -1.0 mA$)	V _{OH}	2.00	$LV_{DD}/TV_{DD} + 0.3$	V	—
Output low voltage ($LV_{DD}/TV_{DD} = Min, I_{OL} = 1.0 mA$)	V _{OL}	GND – 0.3	0.40	V	—
Input high voltage	V _{IH}	1.70	$LV_{DD}/TV_{DD} + 0.3$	V	—
Input low voltage	V _{IL}	-0.3	0.70	V	—



Figure 17 shows the TBI receive the timing diagram.



Figure 17. TBI Single-Clock Mode Receive AC Timing Diagram

8.2.6 **RGMII and RTBI AC Timing Specifications**

Table 34 presents the RGMII and RTBI AC timing specifications.

Table 34. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with $\text{LV}_{\text{DD}}/\text{TV}_{\text{DD}}$ of 2.5 V ± 5%.

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
Data to clock output skew (at transmitter)	t _{SKRGT}	-500	0	500	ps
Data to clock input skew (at receiver) ²	t _{SKRGT}	1.0	—	2.8	ns
Clock period ³	t _{RGT}	7.2	8.0	8.8	ns
Duty cycle for 10BASE-T and 100BASE-TX ^{3, 4}	t _{RGTH} /t _{RGT}	40	50	60	%
Rise time (20%–80%)	t _{rgtr}	—	—	0.75	ns
Fall time (20%–80%)	t _{RGTF}	_	_	0.75	ns

Notes:

- 1. Note that, in general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).
- 2. This implies that PC board design requires clocks to be routed such that an additional trace delay of greater than 1.5 ns will be added to the associated clock signal.
- 3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
- 4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between.



Ethernet: Enhanced Three-Speed Ethernet (eTSEC)

Table 36. RMII Receive AC Timing Specifications (continued)

At recommended operating conditions with LV_DD/TV_DD of 2.5/ 3.3 V \pm 5%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
RXD[1:0], CRS_DV, RX_ER hold time to TSECn_TX_CLK rising edge	t _{RMRDX}	2.0	—	_	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of t_{(first two letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).}

Figure 20 provides the AC test load for eTSEC.



Figure 20. eTSEC AC Test Load

Figure 21 shows the RMII receive AC timing diagram.



Figure 21. RMII Receive AC Timing Diagram

8.3 SGMII Interface Electrical Characteristics

Each SGMII port features a 4-wire AC-Coupled serial link from the dedicated SerDes 2 interface of MPC8572E as shown in Figure 22, where C_{TX} is the external (on board) AC-Coupled capacitor. Each output pin of the SerDes transmitter differential pair features 50- Ω output impedance. Each input of the SerDes receiver differential pair features 50- Ω on-die termination to SGND_SRDS2 (xcorevss). The reference circuit of the SerDes transmitter and receiver is shown in Figure 54.

When an eTSEC port is configured to operate in SGMII mode, the parallel interface's output signals of this eTSEC port can be left floating. The input signals should be terminated based on the guidelines



Ethernet: Enhanced Three-Speed Ethernet (eTSEC)





Table 39 lists the SGMII DC receiver electrical characteristics.

Parameter		Symbol	Min	Тур	Max	Unit	Notes
Supply Voltage		XV _{DD_SRDS2}	1.045	1.1	1.155	V	_
DC Input voltage range		_		N/A		—	1
Input differential voltage	LSTS = 0	V _{RX_DIFFp-p}	100	—	1200	mV	2, 4
	LSTS = 1		175	—			
Loss of signal threshold	LSTS = 0	VLOS	30	—	100	mV	3, 4
	LSTS = 1		65	—	175		
Input AC common mode v	oltage	V _{CM_ACp-p}		—	100	mV	5
Receiver differential input	impedance	Z _{RX_DIFF}	80	100	120	Ω	
Receiver common mode in impedance	nput	Z _{RX_CM}	20	—	35	Ω	—
Common mode input volta	ige	V _{CM}	_	V _{xcorevss}	_	V	6

Table 39. SGMII DC Receiver Electrical Characteristics

Note:

1. Input must be externally AC-coupled.

2. V_{RX DIFFp-p} is also referred to as peak to peak input differential voltage

3. The concept of this parameter is equivalent to the Electrical Idle Detect Threshold parameter in PCI Express. Refer to PCI Express Differential Receiver (RX) Input Specifications section for further explanation.

4. The LSTS shown in the table refers to the LSTSAB or LSTSEF bit field of MPC8572E's SerDes 2 Control Register.

5. $V_{\mbox{CM}_\mbox{ACp-p}}$ is also referred to as peak to peak AC common mode voltage.

6. On-chip termination to SGND_SRDS2 (xcorevss).



10 Local Bus Controller (eLBC)

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8572E.

10.1 Local Bus DC Electrical Characteristics

Table 46 provides the DC electrical characteristics for the local bus interface operating at $BV_{DD} = 3.3 \text{ V}$ DC.

Parameter	Symbol	Min	Max	Unit
Supply voltage 3.3V	BV _{DD}	3.13	3.47	V
High-level input voltage	V _{IH}	2	BV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.8	V
Input current ($BV_{IN}^{1} = 0 V \text{ or } BV_{IN} = BV_{DD}$)	I _{IN}	_	±5	μA
High-level output voltage (BV _{DD} = min, I _{OH} = -2 mA)	V _{OH}	BV _{DD} – 0.2	—	V
Low-level output voltage (BV _{DD} = min, I _{OL} = 2 mA)	V _{OL}	_	0.2	V

 Table 46. Local Bus DC Electrical Characteristics (3.3 V DC)
 Image: Comparison of the second sec

Note:

1. Note that the symbol BV_{IN} , in this case, represents the BV_{IN} symbol referenced in Table 1.

Table 47 provides the DC electrical characteristics for the local bus interface operating at $BV_{DD} = 2.5 V DC$.

Table 47. Local Bus DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Мах	Unit
Supply voltage 2.5V	BV _{DD}	2.37	2.63	V
High-level input voltage	V _{IH}	1.70	BV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.7	V
Input current	I _{IH}	—	10	μΑ
$(BV_{IN} = 0 V \text{ of } BV_{IN} = BV_{DD})$	Ι _{ΙL}		-15	
High-level output voltage (BV _{DD} = min, I _{OH} = -1 mA)	V _{OH}	2.0	BV _{DD} + 0.3	V
Low-level output voltage (BV _{DD} = min, I _{OL} = 1 mA)	V _{OL}	GND – 0.3	0.4	V

Note:

1. The symbol BV_{IN} , in this case, represents the BV_{IN} symbol referenced in Table 1.



Local Bus Controller (eLBC)

Table 48 provides the DC electrical characteristics for the local bus interface operating at $BV_{DD} = 1.8 V$ DC.

Parameter	Symbol	Min	Мах	Unit
Supply voltage 1.8V	BV _{DD}	1.71	1.89	V
High-level input voltage	V _{IH}	0.65 x BV _{DD}	BV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.35 x BV _{DD}	V
Input current ($BV_{IN}^{1} = 0 V \text{ or } BV_{IN} = BV_{DD}$)	I _{IN}	TBD	TBD	μA
High-level output voltage $(I_{OH} = -100 \ \mu A)$	V _{OH}	BV _{DD} – 0.2	—	V
High-level output voltage $(I_{OH} = -2 \text{ mA})$	V _{OH}	BV _{DD} – 0.45	—	V
Low-level output voltage (I _{OL} = 100 μA)	V _{OL}	_	0.2	V
Low-level output voltage (I _{OL} = 2 mA)	V _{OL}	_	0.45	V

Table 48. Local Bus DC Electrical Characteristics (1.8 V DC)

Note:

1. The symbol BV_{IN} , in this case, represents the BV_{IN} symbol referenced in Table 1.

10.2 Local Bus AC Electrical Specifications

Table 49 describes the general timing parameters of the local bus interface at $BV_{DD} = 3.3 \text{ V DC}$.

Table 49. Local Bus General Timing Parameters ($BV_{DD} = 3.3 V DC$)—PLL EnabledAt recommended operating conditions with BV_{DD} of 3.3 V ± 5%.

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	t _{LBK}	6.67	12	ns	2
Local bus duty cycle	t _{LBKH/} t _{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	t _{LBKSKEW}	—	150	ps	7,8
Input setup to local bus clock (except LGTA/LUPWAIT)	t _{LBIVKH1}	1.8	—	ns	3, 4
LGTA/LUPWAIT input setup to local bus clock	t _{LBIVKH2}	1.7	—	ns	3, 4
Input hold from local bus clock (except LGTA/LUPWAIT)	t _{LBIXKH1}	1.0	—	ns	3, 4
LGTA/LUPWAIT input hold from local bus clock	t _{LBIXKH2}	1.0	—	ns	3, 4
LALE output negation to high impedance for LAD/LDP (LATCH hold time)	t _{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	t _{LBKHOV1}	—	2.3	ns	—
Local bus clock to data valid for LAD/LDP	t _{LBKHOV2}	—	2.4	ns	3
Local bus clock to address valid for LAD	t _{LBKHOV3}	—	2.3	ns	3



11 Programmable Interrupt Controller

In IRQ edge trigger mode, when an external interrupt signal is asserted (according to the programmed polarity), it must remain asserted for at least 3 system clocks (SYSCLK periods).

12 JTAG

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the MPC8572E.

Table 53 provides the JTAG AC timing specifications as defined in Figure 37 through Figure 39.

Table 53. JTAG	AC Timina	Specifications	(Independent	t of SYSCLK)	1
	/ · · · · · · · · · · · · · · · · · · ·	opeenieanene	(

At recommended operating conditions with OV_{DD} of 3.3 V ± 5%.

Parameter	Symbol ²	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f _{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t _{JTG}	30	_	ns	—
JTAG external clock pulse width measured at 1.4 V	t _{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t _{JTGR} & t _{JTGF}	0	2	ns	6
TRST assert time	t _{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	t _{JTDVKH} t _{JTIVKH}	4 0		ns	4
Input hold times: Boundary-scan data TMS, TDI	t _{JTDXKH} t _{JTIXKH}	20 25		ns	4
Valid times: Boundary-scan data TDO	t _{jtkldv} t _{jtklov}	4 4	20 25	ns	5
Output hold times: Boundary-scan data TDO	t _{jtkldx} t _{jtklox}	30 30		ns	5



High-Speed Serial Interfaces (HSSI)

15 High-Speed Serial Interfaces (HSSI)

The MPC8572E features two Serializer/Deserializer (SerDes) interfaces to be used for high-speed serial interconnect applications. The SerDes1 interface can be used for PCI Express and/or Serial RapidIO data transfers. The SerDes2 is dedicated for SGMII application.

This section describes the common portion of SerDes DC electrical specifications, which is the DC requirement for SerDes Reference Clocks. The SerDes data lane's transmitter and receiver reference circuits are also shown.

15.1 Signal Terms Definition

The SerDes utilizes differential signaling to transfer data across the serial link. This section defines terms used in the description and specification of differential signals.

Figure 43 shows how the signals are defined. For illustration purpose, only one SerDes lane is used for description. The figure shows waveform for either a transmitter output (SDn_TX and SDn_TX) or a receiver input (SDn_RX and $\overline{SDn_RX}$). Each signal swings between A Volts and B Volts where A > B.

Using this waveform, the definitions are as follows. To simplify illustration, the following definitions assume that the SerDes transmitter and receiver operate in a fully symmetrical differential signaling environment.

1. Single-Ended Swing

The transmitter output signals and the receiver input signals SDn_TX, SDn_TX, SDn_RX and SDn_RX each have a peak-to-peak swing of A - B Volts. This is also referred as each signal wire's Single-Ended Swing.

2. Differential Output Voltage, V_{OD} (or Differential Output Swing):

The Differential Output Voltage (or Swing) of the transmitter, V_{OD} , is defined as the difference of the two complimentary output voltages: $V_{SDn_TX} - V_{\overline{SDn_TX}}$. The V_{OD} value can be either positive or negative.

3. Differential Input Voltage, V_{ID} (or Differential Input Swing):

The Differential Input Voltage (or Swing) of the receiver, V_{ID} , is defined as the difference of the two complimentary input voltages: $V_{SDn_RX} - V_{\overline{SDn_RX}}$. The V_{ID} value can be either positive or negative.

4. Differential Peak Voltage, V_{DIFFp}

The peak value of the differential transmitter output signal or the differential receiver input signal is defined as Differential Peak Voltage, $V_{DIFFp} = |A - B|$ Volts.

5. Differential Peak-to-Peak, V_{DIFFp-p}

Because the differential output signal of the transmitter and the differential input signal of the receiver each range from A – B to –(A – B) Volts, the peak-to-peak value of the differential transmitter output signal or the differential receiver input signal is defined as Differential Peak-to-Peak Voltage, $V_{DIFFp-p} = 2*V_{DIFFp} = 2*|(A – B)|$ Volts, which is twice of differential swing in amplitude, or twice of the differential peak. For example, the output differential peak-peak voltage can also be calculated as $V_{TX-DIFFp-p} = 2*|V_{OD}|$.



Package Description

- 5. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
- 6. Parallelism measurement shall exclude any effect of mark on top surface of package.

18.3 Pinout Listings

Table 76 provides the pin-out listing for the MPC8572E 1023 FC-PBGA package.

Table 76. MPC8572E Pinout Listing

Signal	Signal Name Package Pin Number		Pin Type	Power Supply	Notes
	DDR SDRAM Memo	bry Interface 1			
D1_MDQ[0:63]	Data	D15, A14, B12, D12, A15, B15, B13, C13, C11, D11, D9, A8, A12, A11, A9, B9, F11, G12, K11, K12, E10, E9, J11, J10, G8, H10, L10, M11, F10, G9, K9, K8, AC6, AC7, AG8, AH9, AB6, AB8, AE9, AF9, AL8, AM8, AM10, AK11, AH8, AK8, AJ10, AK10, AL12, AJ12, AL14, AK14, AL11, AM11, AK13, AM14, AM15, AJ16, AL18, AM18, AJ15, AL15, AK17, AM17	I/O	GV _{DD}	_
D1_MECC[0:7]	Error Correcting Code	M10, M7, R8, T11, L12, L11, P9, R10	I/O	GV _{DD}	—
D1_MAPAR_ERR	Address Parity Error	P6	I	GV _{DD}	_
D1_MAPAR_OUT	Address Parity Out	W6	0	GV _{DD}	_
D1_MDM[0:8]	Data Mask	C14, A10, G11, H9, AD7, AJ9, AM12, AK16, N11	0	GV _{DD}	_
D1_MDQS[0:8]	Data Strobe	A13, C10, H12, J7, AE8, AM9, AM13, AL17, N9	I/O	GV _{DD}	_
D1_MDQS[0:8]	Data Strobe	D14, B10, H13, J8, AD8, AL9, AJ13, AM16, P10	I/O	GV _{DD}	_
D1_MA[0:15]	Address	Y7, W8, U6, W9, U7, V8, Y11, V10, T6, V11, AA10, U9, U10, AD11, T8, P7	0	GV _{DD}	
D1_MBA[0:2]	Bank Select	AA7, AA8, R7	0	GV_DD	
D1_MWE	Write Enable	AC12	0	GV _{DD}	—



Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
D1_MCAS	Column Address Strobe	AC9	0	GV _{DD}	
D1_MRAS	Row Address Strobe	AB12	0	GV _{DD}	
D1_MCKE[0:3]	Clock Enable	M8, L9, T9, N8	0	GV _{DD}	11
D1_MCS[0:3]	Chip Select	AB9, AF10, AB11, AE11	0	GV _{DD}	_
D1_MCK[0:5]	Clock	V7, E13, AH11, Y9, F14, AG10	0	GV _{DD}	
D1_MCK[0:5]	Clock Complements	Y10, E12, AH12, AA11, F13, AG11	0	GV _{DD}	
D1_MODT[0:3]	On Die Termination	AD10, AF12, AC10, AE12	0	GV _{DD}	_
D1_MDIC[0:1]	Driver Impedance Calibration	E15, G14	I/O	GV _{DD}	25
	DDR SDRAM Mem	ory Interface 2		•	
D2_MDQ[0:63]	Data	A6, B7, C5, D5, A7, C8, D8, D6, C4, A3, D3, D2, B4, A4, B1, C1, E3, E1, G2, G6, D1, E4, G5, G3, J4, J2, P4, R5, H3, H1, N5, N3, Y6, Y4, AC3, AD2, V5, W5, AB2, AB3, AD5, AE3, AF6, AG7, AC4, AD4, AF4, AF7, AH5, AJ1, AL2, AM3, AH3, AH6, AM1, AL3, AK5, AL5, AJ7, AK7, AK4, AM4, AL6, AM7	I/O	GV _{DD}	_
D2_MECC[0:7]	Error Correcting Code	J5, H7, L7, N6, H4, H6, M4, M5	I/O	GV _{DD}	
D2_MAPAR_ERR	Address Parity Error	N1	Ι	GV _{DD}	
D2_MAPAR_OUT	Address Parity Out	W2	0	GV _{DD}	
D2_MDM[0:8]	Data Mask	A5, B3, F4, J1, AA4, AE5, AK1, AM5, K5	0	GV _{DD}	
D2_MDQS[0:8]	Data Strobe	B6, C2, F5, L4, AB5, AF3, AL1, AM6, L6	I/O	GV _{DD}	_
D2_MDQS[0:8]	Data Strobe	C7, A2, F2, K3, AA5, AE6, AK2, AJ6, K6	I/O	GV _{DD}	—
D2_MA[0:15]	Address	W1, U4, U3, T1, T2, T3, R1, R2, T5, R4, Y3, P1, N2, AF1, M2, M1	0	GV _{DD}	_

Table 76. MPC8572E Pinout Listing (continued)

Table 78. Memory Bus Clocking Specifications

Characteristic	Min	Мах	Unit	Notes
Memory bus clock frequency	200	400	MHz	1, 2, 3, 4

Notes:

- 1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 19.2, "CCB/SYSCLK PLL Ratio," Section 19.3, "e500 Core PLL Ratio," and Section 19.4, "DDR/DDRCLK PLL Ratio," for ratio settings.
- 2. The Memory bus clock refers to the MPC8572E memory controllers' Dn_MCK[0:5] and Dn_MCK[0:5] output clocks, running at half of the DDR data rate.
- 3. In synchronous mode, the memory bus clock speed is half the platform clock frequency. In other words, the DDR data rate is the same as the platform (CCB) frequency. If the desired DDR data rate is higher than the platform (CCB) frequency, asynchronous mode must be used.
- 4. In asynchronous mode, the memory bus clock speed is dictated by its own PLL. Refer to Section 19.4, "DDR/DDRCLK PLL Ratio." The memory bus clock speed must be less than or equal to the CCB clock rate which in turn must be less than the DDR data rate.

As a general guideline when selecting the DDR data rate or platform (CCB) frequency, the following procedures can be used:

- Start with the processor core frequency selection;
- After the processor core frequency is determined, select the platform (CCB) frequency from the limited options listed in Table 80 and Table 81;
- Check the CCB to SYSCLK ratio to verify a valid ratio can be choose from Table 79;
- If the desired DDR data rate can be same as the CCB frequency, use the synchronous DDR mode; Otherwise, if a higher DDR data rate is desired, use asynchronous mode by selecting a valid DDR data rate to DDRCLK ratio from Table 82. Note that in asynchronous mode, the DDR data rate must be greater than the platform (CCB) frequency. In other words, running DDR data rate lower than the platform (CCB) frequency in asynchronous mode is not supported by MPC8572E.
- Verify all clock ratios to ensure that there is no violation to any clock and/or ratio specification.

19.2 CCB/SYSCLK PLL Ratio

The CCB clock is the clock that drives the e500 core complex bus (CCB), and is also called the platform clock. The frequency of the CCB is set using the following reset signals, as shown in Table 79:

- SYSCLK input signal
- Binary value on LA[29:31] at power up

Note that there is no default for this PLL ratio; these signals must be pulled to the desired values. Also note that, in synchronous mode, the DDR data rate is the determining factor in selecting the CCB bus frequency, because the CCB frequency must equal the DDR data rate. In asynchronous mode, the memory bus clock frequency is decoupled from the CCB bus frequency.



System Design Information

21.6 Pull-Up and Pull-Down Resistor Requirements

The MPC8572E requires weak pull-up resistors (2–10 k Ω is recommended) on open drain type pins including I²C pins and MPIC interrupt pins.

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 66. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion gives unpredictable results.

The following pins must NOT be pulled down during power-on reset: DMA_DACK[0:1], EC5_MDC, HRESET_REQ, TRIG_OUT/READY_P0/QUIESCE, MSRCID[2:4], MDVAL, and ASLEEP. The TEST_SEL pin must be set to a proper state during POR configuration. For more details, refer to the pinlist table of the individual device.

21.7 Output Buffer DC Impedance

The MPC8572E drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 64). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.



Figure 64. Driver Impedance Measurement



22 Ordering Information

Ordering information for the parts fully covered by this specification document is provided in Section 22.1, "Part Numbers Fully Addressed by this Document."

22.1 Part Numbers Fully Addressed by this Document

Table 86 through Table 88 provide the Freescale part numbering nomenclature for the MPC8572E. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. In addition to the processor frequency, the part numbering scheme also includes an application modifier which may specify special application conditions. Each part number also contains a revision code which refers to the die mask revision number.

MPC	nnnn	е	t	1	рр	ffm	r
Product Code ¹	Part Identifier	Security Engine	Temperature	Power	Package Sphere Type ²	Processor Frequency/ DDR Data Rate ³	Silicon Revision
MPC PPC	8572	E = Included	Blank = 0 to 105°C C = −40 to 105°C	Blank = Standard L = Low	PX = Leaded, FC-PBGA VT = Pb-free, FC-PBGA ⁴ VJ = Fully Pb-free FC-PBGA ⁵	AVN = 1500-MHz processor; 800 MT/s DDR data rate AUL = 1333-MHz processor; 667 MT/s DDR data rate ATL = 1200-MHz processor; 667 MT/s DDR data rate ARL = 1067-MHz processor; 667 MT/s DDR data rate	E = Ver. 2.2.1 (SVR = 0x80E8_0022) SEC included
		Blank = Not included					E = Ver. 2.2.1 (SVR = 0x80E0_0022) SEC not included

Notes:

- ¹ MPC stands for "Qualified."
- PPC stands for "Prototype"
- ² See Section 18, "Package Description," for more information on the available package types.
- ³ Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.
- 4. The VT part number is ROHS-compliant with the permitted exception of the C4 die bumps.
- 5. The VJ part number is entirely lead-free. This includes the C4 die bumps.



Ordering Information

MPC	nnnn	е	t	1	рр	ffm	r
Product Code ¹	Part Identifier	Security Engine	Temperature	Power	Package Sphere Type ²	Processor Frequency/ DDR Data Rate ³	Silicon Revision
MPC PPC	8572	$\begin{tabular}{ c c c c c } \hline E &= & Included \\ \hline E &= & Included \\ \hline C &= & -40 \ to \ 105^{\circ}C \\ \hline C &= & -40 \ to \ 105^{\circ}C \\ \hline C &= & Leade \\ \hline Standard \\ L &= & Low \\ \hline VT &= \\ FC-Pl $	PX = Leaded, FC-PBGA VT = Pb-free,	AVN = 150- MHz processor; 800 MT/s DDR data rate	D= Ver. 2.1 (SVR = 0x80E8_0021) SEC included		
						AUL = 1333-MHz processor; 667 MT/s DDR data rate ATL = 1200-MHz processor; 667 MT/s DDR data rate	D= Ver. 2.1 (SVR = 0x80E0_0021) SEC not included
						ARL = 1067-MHz processor; 667 MT/s DDR data rate	

Table 87. Part Numbering Nomenclature—Rev 2.1

Notes:

¹ MPC stands for "Qualified."

PPC stands for "Prototype"

² See Section 18, "Package Description," for more information on the available package types.

³ Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.

Table 88. Part Numbering Nomenclature—Rev 1.1.1

MPC	nnnn	е	t	рр	ffm	r
Product Code ¹	Part Identifier	Security Engine	Temperature	Package Sphere Type ²	Processor Frequency/ DDR Data Rate ³	Silicon Revision
MPC PPC	8572	E = Included Blank = Not included	Blank=0 to 105°C C= −40 to 105°C	PX = Leaded, FC-PBGA VT = Pb-free, FC-PBGA	AVN = 1500-MHz processor; 800 MT/s DDR data rate AUL = 1333-MHz process or; 667 MT/s DDR datarate ATL = 1200-MHz processor; 667 MT/s DDR data rate ARL = 1067-MHz processor; 667 MT/s DDR data rate	B = Ver. 1.1.1 (SVR = 0x80E8_0011) SEC included B = Ver. 1.1.1 (SVR = 0x80E0_0011) SEC not included

Notes:

¹ MPC stands for "Qualified."

PPC stands for "Prototype"

² See Section 18, "Package Description," for more information on the available package types.